

DESCRIPTION

The MXT023N10TAL uses advanced trench technology to provide excellent $R_{DS(ON)}$ with low gate charge. It can be used in a wide variety of applications.

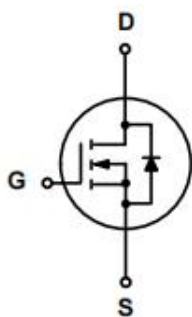
GENERAL FEATURES

- $V_{DS}=100V$, $I_D=280A$
 $R_{DS(ON)}(Typ.)=2.0m\Omega @ V_{GS}=10V$
- Advanced trench cell design
- Super-mounted package

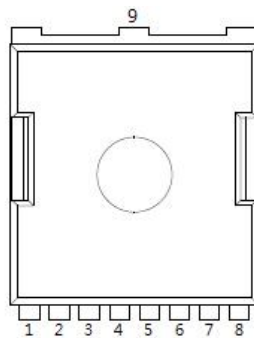
APPLICATION

- LCD TV appliances
- High power inverter system
- LCDM appliances

PINOUT



Schematic diagram



TOLL-8L top view

Pin	Description
1	Gate(G)
2,3,4,5,6,7,8	Source(S)
9	Drain(D)

ORDERING INFORMATION

Part Number	Storage Temperature	Package	Devices Per Reel
MXT023N10TAL	-55°C to 175°C	TOLL-8L	2000

ABSOLUTE MAXIMUM RATINGS ($T_C=25^\circ C$ unless otherwise noted)

Parameter	Symbol	Limit	Unit
Drain-Source Voltage	V_{DS}	100	V
Gate-Source Voltage	V_{GS}	± 20	V
Drain Current ($V_{GS}=10V$)	I_D	280	A
Drain Current ($T_C=100^\circ C$, $V_{GS}=10V$)	I_D	186	A
Pulsed Drain Current ($V_{GS}=10V$) ^(Note1)	I_{DM}	1000	A
Diode Forward Current	I_S	280	A
Drain Power Dissipation	P_{tot}	286	W
Operating Junction and Storage Temperature Range	T_J , T_{STG}	-55 to 175	°C
Single Pulsed Avalanche Energy	E_{AS}	1750	mJ
Thermal Resistance, Junction-to-Ambient ^(Note2)	$R_{\theta JA}$	40	°C/W
Thermal Resistance, Junction-to-Case ^(Note2)	$R_{\theta JC}$	0.25	°C/W

Note 1. Pulse width $\leq 300\mu s$, duty cycle $\leq 2\%$

Note 2. Surface Mounted on minimum footprint pad area



N-Channel Enhancement Mode Power MOSFET **MXT023N10TAL**



ELECTRICAL CHARACTERISTICS ($T_A=25^\circ\text{C}$ unless otherwise noted)

Parameter	Symbol	Conditions	Min	Typ	Max	Unit
Off Characteristics						
Drain-Source Breakdown Voltage	BV_{DSS}	$V_{GS}=0V, I_D=250\mu A$	100	-	-	V
Zero Gate Voltage Drain Current	I_{DSS}	$V_{DS}=80V, V_{GS}=0V$	-	-	1	μA
Gate-Body Leakage Current	I_{GSS}	$V_{GS}=\pm 20V, V_{DS}=0V$	-	-	± 100	nA
On Characteristics						
Gate Threshold Voltage	$V_{GS(th)}$	$V_{DS}=V_{GS}, I_D=250\mu A$	2.0	-	4.0	V
On-State Resistance ^(Note1)	$R_{DS(ON)}$	$V_{GS}=10V, I_D=20A$	-	2.0	2.3	m Ω
Dynamic Characteristics ^(Note2)						
Input Capacitance	C_{iss}	$V_{DS}=50V, V_{GS}=0V, F=1.0MHz$	-	7884	-	pF
Output Capacitance	C_{oss}		-	1240	-	pF
Reverse Transfer Capacitance	C_{rss}		-	30	-	pF
Switching Characteristics ^(Note2)						
Turn-on Delay Time	$t_{d(on)}$	$V_{DS}=50V, I_{DS}=20A, V_{GEN}=10V, R_G=4.5\Omega, R_L=2.5\Omega,$	-	26	-	nS
Turn-on Rise Time	t_r		-	55	-	nS
Turn-Off Delay Time	$t_{d(off)}$		-	72	-	nS
Turn-Off Fall Time	t_f		-	66	-	nS
Total Gate Charge	Q_g	$V_{DS}=50V, I_{DS}=20A, V_{GS}=10V$	-	122	-	nC
Gate-Source Charge	Q_{gs}		-	32	-	nC
Gate-Drain Charge	Q_{gd}		-	31	-	nC
Drain-Source Diode Characteristics						
Diode Forward Voltage ^(Note1)	V_{SD}	$V_{GS}=0V, I_{SD}=20A$	-	-	1.3	V
Reverse Recovery Time	t_{rr}	$I_{DS}=20A, V_{GS}=0V$	-	96	-	nS
Reverse Recovery Charge	Q_{rr}	$di_{SD}/dt=100A/\mu s$	-	235	-	nC

Note 1. The data tested by pulsed , pulse width $\leq 300\mu s$, duty cycle $\leq 2\%$

Note 2. Guaranteed by design, not subject to production testing

TYPICAL ELECTRICAL AND THERMAL CHARACTERISTICS

Figure 1. Power Capability

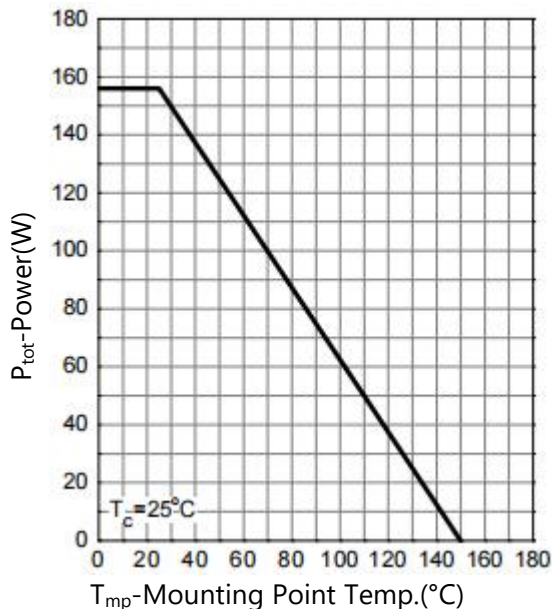


Figure 2. Current Capability

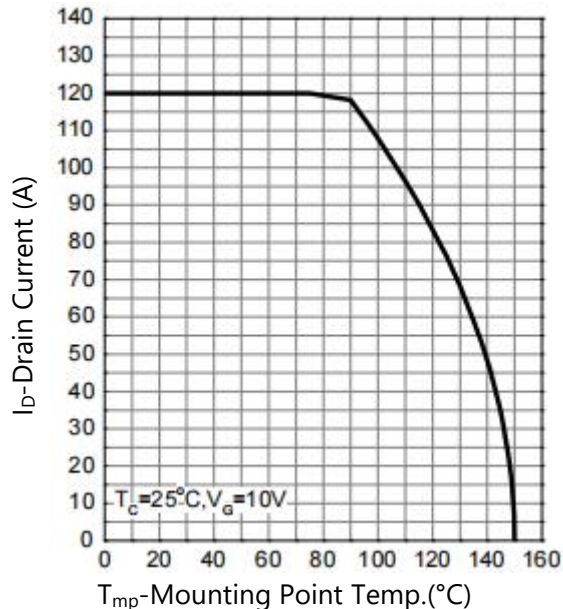


Figure 3. Safe Operation Area

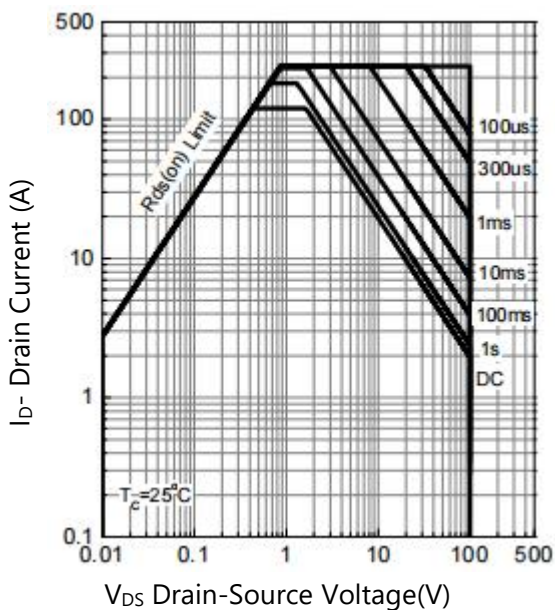
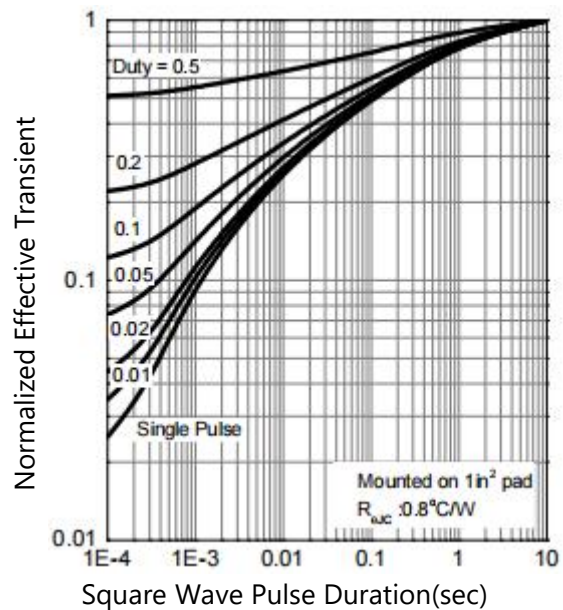


Figure 4. Transient Thermal Impedance





TYPICAL ELECTRICAL AND THERMAL CHARACTERISTICS

Figure 5. Output Characteristics

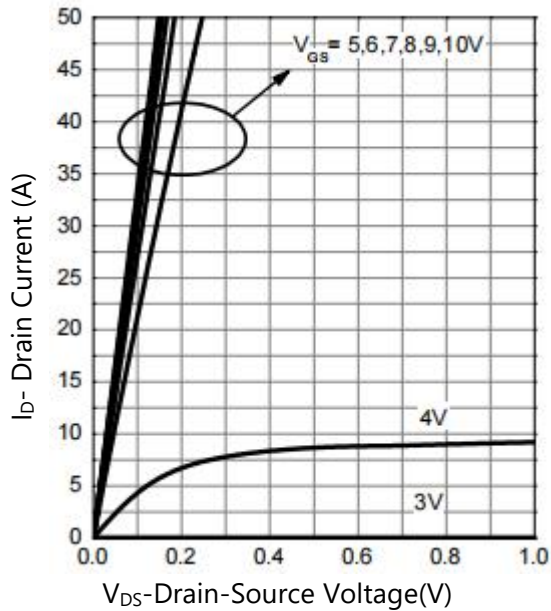


Figure 6. On Resistance

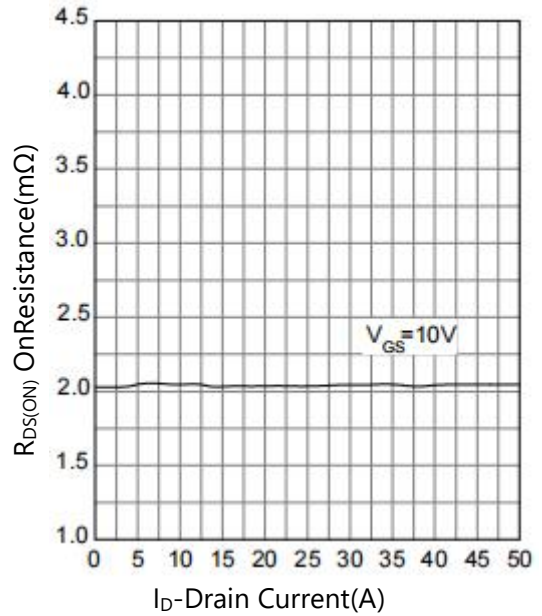


Figure 7. Transfer Characteristics

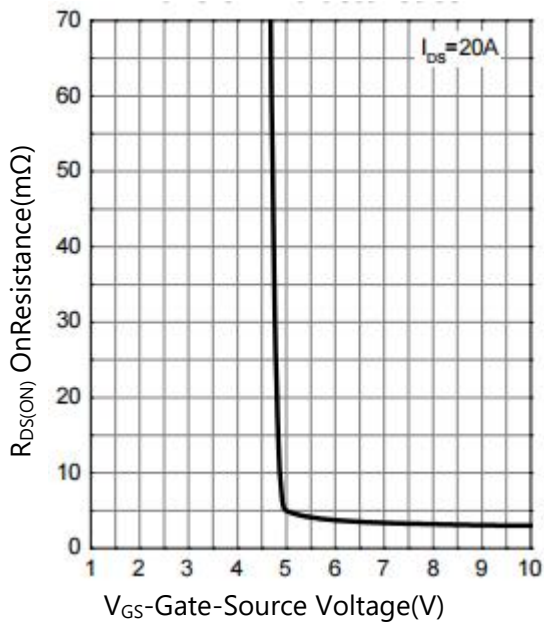
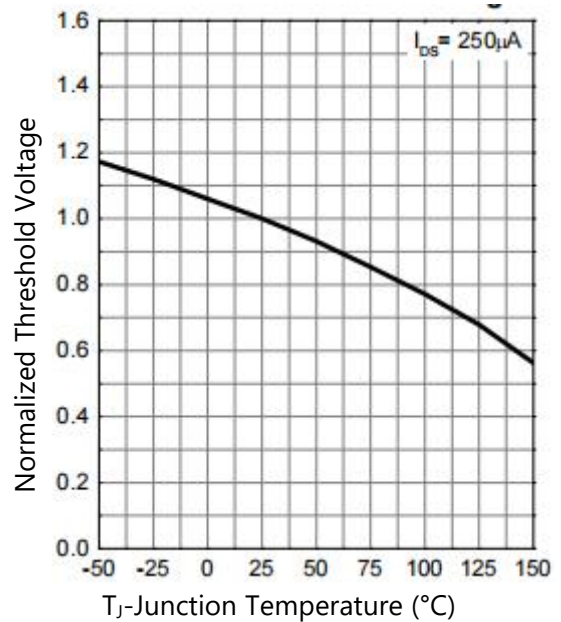


Figure 8. Normalized Threshold Voltage





TYPICAL ELECTRICAL AND THERMAL CHARACTERISTICS

Figure 9. Normalized On Resistance

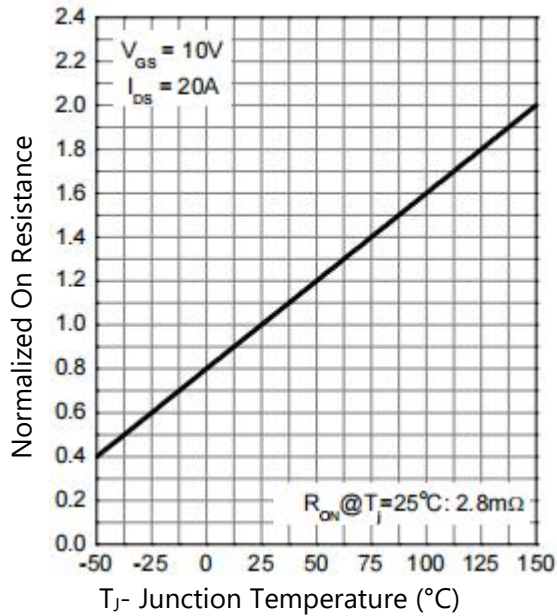


Figure 10. Diode Forward Current

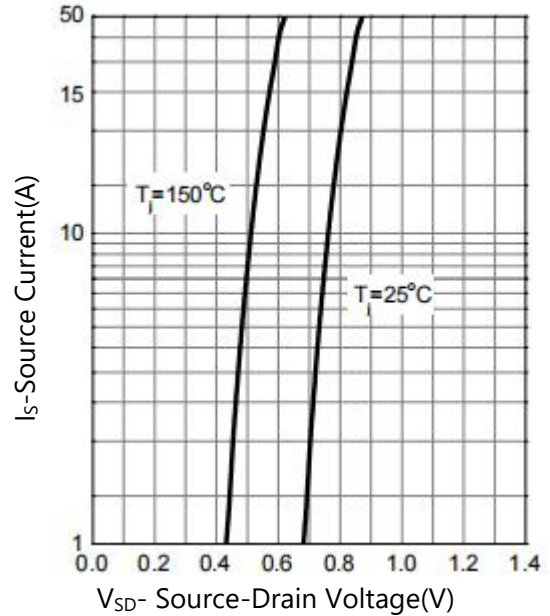


Figure 11. Capacitance

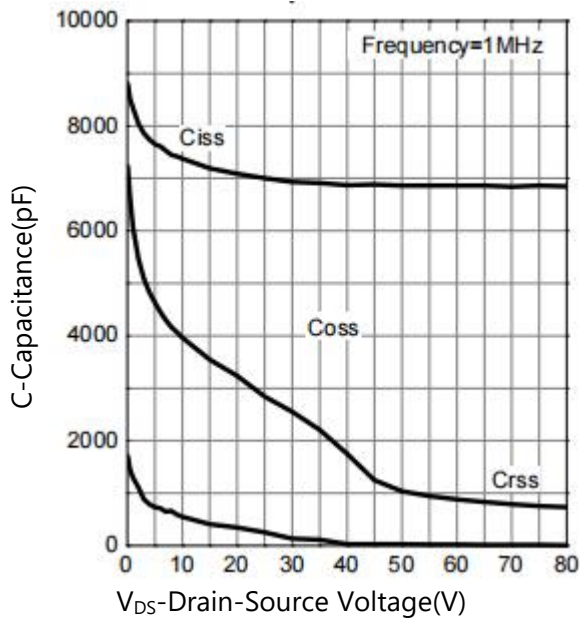
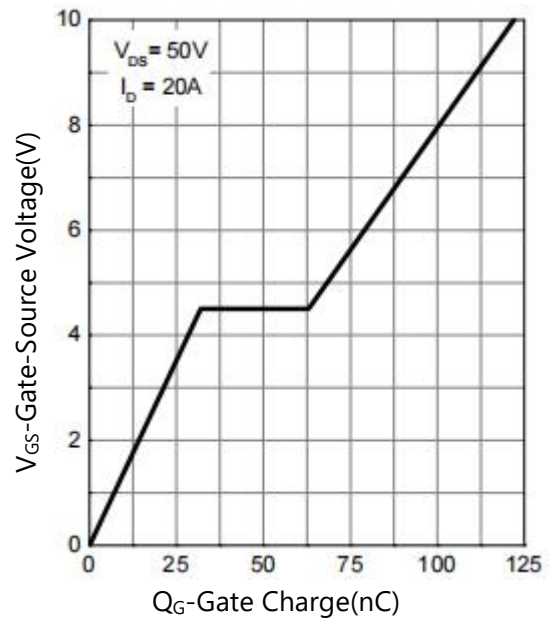
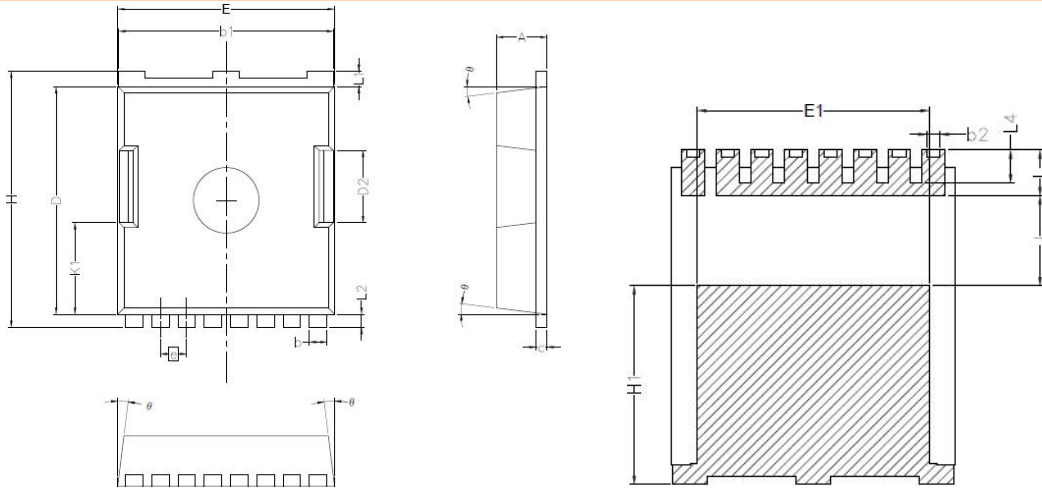


Figure 12. Gate Charge



PACKAGE INFORMATION

TOLL-8L



Symbol	Dimensions In Millimeters	
	MIN.	MAX.
A	2.20	2.40
b	0.90	0.90
b1	9.70	9.90
b2	0.42	0.50
c	0.40	0.60
D	10.28	10.58
D2	3.10	3.50
E	9.70	10.10
E1	7.90	8.30
e	1.20BSC	
H	11.48	11.88
H1	6.75	7.15
N	8	
J	3.00	3.30
K1	3.98	4.38
L	1.40	1.80
L1	0.60	0.80
L2	0.50	0.70
L4	1.00	1.30
θ	4°	10°